



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

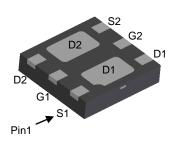
Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	50mΩ @V _{GS} = -4.5V	-4.5A
-20V	100mΩ @V _{GS} = -2.5V	-3.2A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors



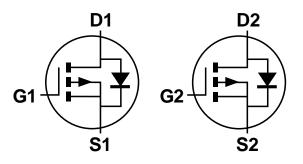
Bottom View

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208[®]
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP2065UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel		
DMP2065UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E	ı	=	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-20	V	
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	T _A = +25°C T _A = +85°C	I _D	-4.5 -3.6	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)		I _{DM}	-25	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 6)		Is	-1.4	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-13	Α
Avalanche Energy (Note 7) L = 0.1mH		E _{AS}	9	mJ	

Thermal Characteristics

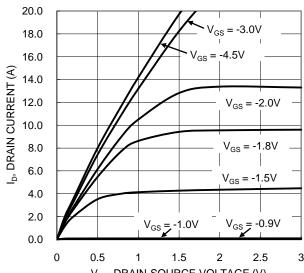
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	D.	171	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	131	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P _D	1.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D.	82	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	60	°C/W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	13	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

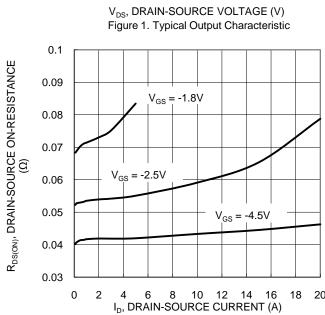
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

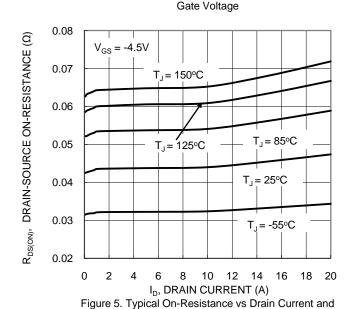
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			40	50		$V_{GS} = -4.5V$, $I_D = -2.0A$
Static Drain-Source On-Resistance	D		55	100	mΩ	$V_{GS} = -2.5V$, $I_D = -2.0A$
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	75	150	11122	$V_{GS} = -1.8V, I_D = -1.6A$
			95	200		$V_{GS} = -1.5V, I_D = -1.0A$
Diode Forward Voltage	V_{SD}		-0.75	-1.1	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}		752		pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance	Coss		87	_	рF	$V_{DS} = -15V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		78	_	рF	1 = 1.01/11/12
Gate Resistance	R_{G}		15.2	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$
Total Gate Charge	Q_{g}		9.1	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Gate-Source Charge	Q_{gs}		1.2	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -4V$, $I_{D} = -3.5A$
Gate-Drain Charge	Q_{gd}		1.9	_	nC	ID = -3.5A
Turn-On Delay Time	t _{D(ON)}		5.4	_	ns	
Turn-On Rise Time	t _R	_	8.3	_	ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,
Turn-Off Delay Time	t _{D(OFF)}		47		ns	$R_G = 6\Omega$, $I_D = -1A$
Turn-Off Fall Time	t _F		20	_	ns	

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

DMP2065UFDB

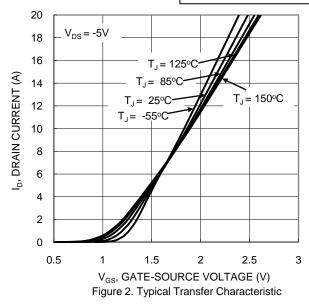


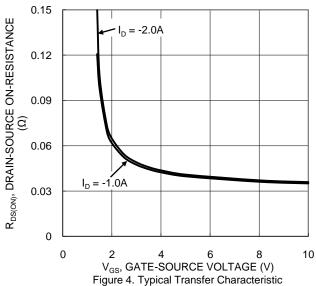




Junction Temperature

Figure 3. Typical On-Resistance vs Drain Current and





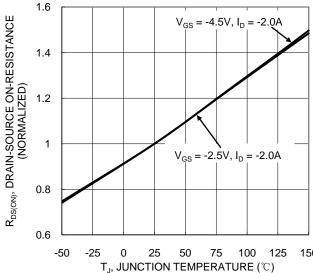


Figure 6. On-Resistance Variation with Junction Temperature



DMP2065UFDB

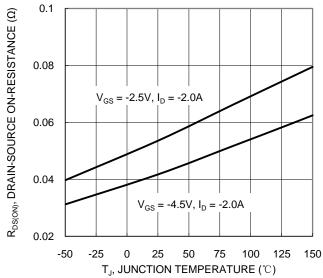


Figure 7. On-Resistance Variation with Junction Temperature

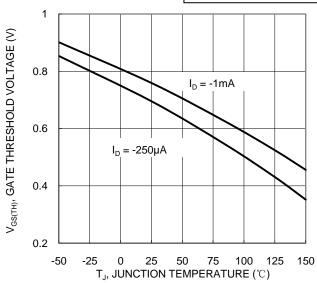
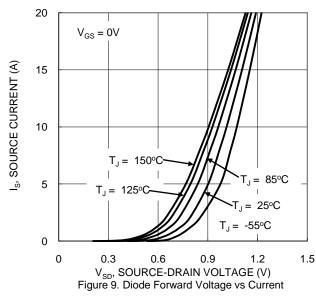
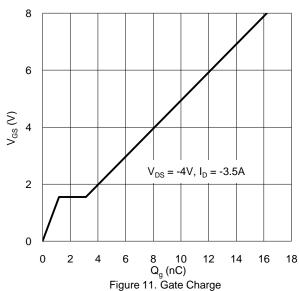
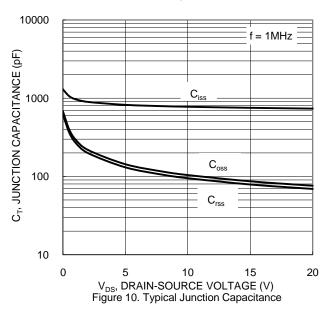
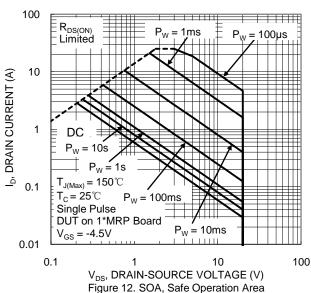


Figure 8. Gate Threshold Variation vs Junction Temperature











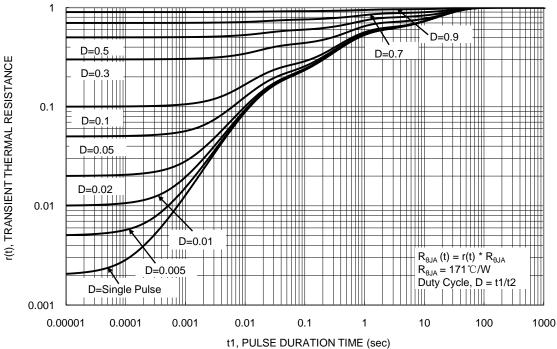


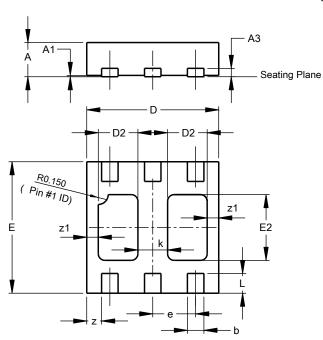
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

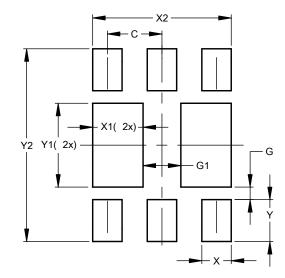


U-DFN2020-6 Type B						
Dim	Min Max Typ					
Α	0.545	0.605	0.575			
A1	0.00	0.05	0.02			
A3	-	-	0.13			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	0.50	0.70	0.60			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.90	1.10	1.00			
k	-	-	0.45			
L	0.25	0.35	0.30			
Z	-	-	0.225			
z1	-	-	0.175			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
Dillielisions	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Υ	0.500
Y1	1.000
Y2	2.300



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